Product specification

NPN Epitaxial Silicon Ttransistors

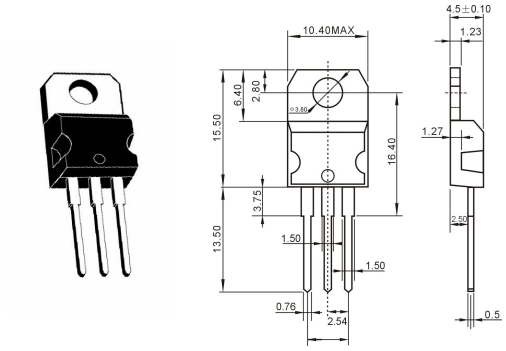
BD241C

Medium Power Linear and Switching Applications

Complement to BD242C respectively

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	3.0	A
Collector Dissipation	P_C	40	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



TO-220M-1

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	V_{CB}= 80V, I_E=0	—	—	0.1	mA
Emitter Cut-off Current	I_{EBO}	V_{EB}= 5.0V, I_C=0	—	—	0.1	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	I_C= 10mA, I_B=0	100	—	—	V
DC Current Gain	$h_{FE(1)}$	V_{CE}= 4.0V, I_C= 1.0A	25	—	—	
	$h_{FE(2)}$	V_{CE}= 4.0V, I_C= 3.0A	10	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= 3.0A,I_B= 600mA	—	—	1.2	V
Base-Emitter ON Voltage	$V_{BE(ON)}$	V_{CE}= 4.0V, I_C= 3.0A	—	—	1.8	V